

WHAT IS CLAIMED IS:

1. A method of making a magnetoresistive head element, comprising:

forming a magnetoresistive film extending over a surface of a substratum, said magnetoresistive film having a side surface standing on the surface of the substratum;

forming an insulating base layer over the surface of the substratum, said insulating base layer contacting at least partly the side surface of the magnetoresistive film; and

effecting an etching process while keeping the insulating base layer contacting the side surface of the magnetoresistive film.

2. The method of making according to claim 1, further comprising:

forming a conductive layer covering over at least the magnetoresistive film and the insulating base layer, prior to the etching process; and

exposing the conductive layer to an etching gas with the side surface of the magnetoresistive film kept covered.

3. The method of making according to claim 1, further comprising:

forming a domain control stripe layer over the surface of the substratum, prior to formation of the insulating base layer, said domain control stripe layer contacting the magnetoresistive film at its tip end; and

allowing the insulating base layer to contact a side surface of the domain control stripe layer adjacent the side surface of the magnetoresistive film.

4. The method of making according to claim 3, further comprising:

forming a conductive layer covering over at least the magnetoresistive film and the insulating base layer, prior to the etching process; and

exposing the conductive layer to an etching gas with the side surface of the magnetoresistive film kept covered.

5. A method of making a magnetoresistive head element, comprising:

forming a layered composite, corresponding to a layered structure of a magnetoresistive film, over a surface of a substratum;

forming a pair of material layers, corresponding to materials of domain control stripe layers, over the surface of the substratum, said material layers interposing the layered composite therebetween along the surface of the substratum;

forming a resist film on the layered composite and the material layers so as to pattern a shape of the magnetoresistive film and the domain control stripe layers continuous one another;

removing the layered composite and the material layers in a region adjacent the resist film so as to shape the magnetoresistive film and the domain control stripe layers out of the layered composite and the material layers below the resist film;

forming an insulating base layer over the resist film and the surface of the substratum; and

removing the resist film so as to expose the magnetoresistive film and the domain control stripe layers at a gap defined in the insulating base layer.

6. The method of making according to claim 5, further comprising: effecting an etching process while keeping the insulating base layer in a region adjacent the magnetoresistive film over the surface of the substratum.

7. The method of making according to claim 6, further comprising:

forming a conductive layer covering over at least the magnetoresistive film and the insulating base layer, prior to the etching process; and

exposing the conductive layer to an etching gas with a side surface of the magnetoresistive film kept covered, said side surface defined to stand on the surface of the substratum.

8. A magnetoresistive head element comprising:

a magnetoresistive film extending over a surface of a substratum so as to define a side surface standing on the surface of the substratum;

a domain control stripe layer connected to the magnetoresistive film at its tip end so as to define a side surface standing adjacent the side surface of the magnetoresistive film on the substratum;

an insulating base layer extending over the surface of the substratum so as to contact the side surface of the magnetoresistive film and the side surface of the domain control stripe layer; and

a conductive lead layer covering over the domain control stripe layer and the insulating base layer.

9. The magnetoresistive head element according to claim

8, wherein said insulating base layer is integrally continuous to a primary insulating layer covering over the magnetoresistive film.